

Form PTO-1449 Department of Commerce Patent and Trademark Office  <b>INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION</b>  (Use several sheets if necessary)	Docket No. <b>PAT034US</b>	Serial No. <b>Unassigned</b>
	Applicants <b>Anselm et al.</b>	
	Filing Date <b>Herewith</b>	Group Art Unit <b>Unassigned</b>

31011 U.S. PTO

09/993239



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## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>Dh</i>	4,949,350	08/14/99	Jewell et al.	<u>          </u>	<u>          </u>	
	5,031,187	07/09/91	Orenstein et al.	<u>          </u>	<u>          </u>	
	5,115,442	05/19/92	Lee et al.	<u>          </u>	<u>          </u>	
	5,193,098	03/09/93	Welch et al.	<u>          </u>	<u>          </u>	
	5,219,785	06/15/93	Welch et al.	<u>          </u>	<u>          </u>	
<i>Dh</i>	5,256,596	10/26/93	Ackley et al.	<u>          </u>	<u>          </u>	

## FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES   NO	

## OTHER (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>Dh</i>	Qian, Y. et al., "Long Wavelength (1.3 $\mu$ m) Vertical-Cavity Surface-Emitting Lasers With a Wafer-Bonded Mirror and an Oxygen-Implanted Confinement Region," <i>Appl. Phys. Lett.</i> , Vol. 71, No. 1, (1997), pp. 25-27.
<i>Dh</i>	Ridgway, M. C., et al., "Single-Step Implant Isolation of p <sup>+</sup> -InP with 5-MeV O Ions," <i>Appl. Phys. Lett.</i> , Vol. 60, No. 24, (1992), pp. 3010-3012.
<i>Dh</i>	Huffaker, D. L. et al., "Native-Oxide Defined Ring Contact for Low Threshold Vertical-Cavity Lasers," <i>Appl. Phys. Lett.</i> , Vol. 65, No. 1, (1994), pp. 97-99.
<i>Dh</i>	Lee, Y. H. et al., "Top-Surface-Emitting GaAs Four-Quantum-Well Lasers Emitting at 0.85 $\mu$ m", <i>Electronics Letters</i> , Vol. 26, No. 11, (1990), pp.710-711.

EXAMINER <i>Dh</i>	DATE CONSIDERED <i>9/2005</i>
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

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<b>U.S. PATENT DOCUMENTS</b>						
*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Dle	5,328,854	07/12/94	Vakhshoori et al.	1	1	
	5,594,751	01/14/97	Scott, Jeffrey W.	1	1	
	5,764,674	06/09/98	Hibbs-Brenner et al.	1	1	
	5,893,722	04/13/99	Hibbs-Brenner et al.	1	1	
	6,044,100	03/28/00	Hobson et al.	1	1	
Dle	6,169,756 B1	01/02/01	Chirovsky et al.	1	1	
<b>FOREIGN PATENT DOCUMENTS</b>						
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES   NO
<b>OTHER (Including Author, Title, Date, Pertinent Pages, Etc.)</b>						
Dle	Choquette, K. D., et al., "Low Threshold Voltage Vertical-Cavity Lasers Fabricated by Selective Oxidation," <i>Electronics Letters</i> , Vol. 30, No. 24, (1994), pp. 2043-2044.					
/	Deng, H. and Deppe, D. G., "Oxide-Confined Vertical-Cavity Lser With Additional Etched Void Confinement," <i>Electronics Letters</i> , Vol. 32, No. 10, (1996), pp. 900-901.					
EXAMINER <span style="float: right;">Dle</span>				DATE CONSIDERED <span style="float: right;">9/2005</span>		
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